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EXAM <b>N</b> INITIAL	PADEMARY	DOCUMENT NUMBER	DATE		NAME	CLASS	SUB CLASS	FILING DATE	
ARS	AA	5,055,138	10/8/91	Slinn		1 0000	CLASS	DATE	
	AB	5,120,370	6/9/92	Mori et al.			<del>                                     </del>		
	AC	5,647,386	7/15/97	Kaiser					
	AD	5,181,985	1/26/93	Lampert et al.					
	AE	5,503,708	4/2/96	Koizumi et al.					
	AF	5,464,480	11/7/95	Matthews					
	AH	5,308,745	5/3/94	Schwartzkopf					
	AI	4,695,327	9/22/87	Grebinski		1			
	AJ	5,632,847	5/27/97	Ohno et al.					
	AK	5,911,837	6/15/99	Matthews					
	AL	5,705,089	1/6/98	Sugihara et al.			V _		
	AM	5,244,000	9/14/93	Stanford et al.			$\Lambda$		
	AN	5,714,203	2/3/98	Schellenberger	et al.				
	AO	5,896,875	4/27/99	Yoneda					
	AP	4,974,530	12/4/90	Lyon		$\bot$		**	
	AQ	5,248,380	9/28/93	Tanaka		$\bot$			
	AR	5,520,744	5/28/96	Fujikawa et al.		$\bot\!\!\!\bot$			
	AS	5,415,191	5/16/95	Mashimo et al.					
	AT	5,658,615	8/19/97	Hasebe et al.		$\perp$		•	
	AU	5,858,107	1/12/99	Chao et al.		<del> </del>			
<u> </u>	AV	5,235,995	8/17/93	Bergman et al.					
748	AW	5,378,317	1/3/95	Kashiwase et al.		<u> </u>	\		
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Information Disclosure Statement – Section 9 PTO-1449

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س	LIST		NTS AND OTHER ITEM			APPLICANT:	I	CA
	6	THE	MATION DISCLOSURE	STATEMEN	T	Eric J. Bergman		Ap.
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	APP	0 9 2002	66					1 1002
NRS		AX PADEMAR AY	971,368	10/26/99	Nelson et al.		\	GROUP:
	1	RADEMAN	5,234,540	8/10/93	Grant et al.		<u> </u>	
		AZ	5,803,982	9/8/98	Kosofsky et al	•	<u> </u>	
		BA	5,944,907	8/31/99	Ohmi		<u> </u>	
		BB	5,232,511	8/3/93	Bergman		1	
	<u> </u>	ВС	5,776,296	7/7/98	Matthews			
		BD	5,071,485	12/10/91	Matthews et al			
	ļ	BE	4,778,532	10/18/88	McConnell et a	al.		-
	<u> </u>	BF	4,899,767	1/13/90	McConnell et a	al.		
		BG	5,964,954	10/12/99	Matsukawa et	al.		
		ВН	5,032,218	7/16/91	Dobson	9		<b>\</b> /
		BI	6,249,933	6/2001	Bergman			<del></del>
	ļ	BJ	6,267,125	7/2001	Bergman et al.		м	A
		BK	6,273,108	8/2001	Bergman et al.			/
		BL	5,950,643	9/1999	Miyazaki et al.			
		BM	6,146,469	11/2000	Toshima	<u>.</u>		
		BN	4,917,123	4/90	McConnell et a	al.		
		ВО	5,105,556	4/92	Kurokawa et a	1.		
		BP	5,326,406	7/94	Kaneko et al.			
	ļ	BQ	4,186,032	1/80	Ham	· · · · · · · · · · · · · · · · · · ·		
		BR	4,749,440	6/88	Blackwood et a	al.		
		BS	4,817,652	4/89	Liu			
		вт	5,832,177	11/98	Shinagawa et a	ıl.		
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Information Disclosure Statement – Section 9 PTO-1449

Page 2 of 5

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		1			<i>/</i>		77	1002	
1765	BW	5,503,708	4/96	RADEMARK of al.			- '(	0	
	BX	5,378,317	1/95	Kashiwase et	al.			-	
Aus	BY	5,571,367	11/96	Nakajima et a	<b>I.</b>				
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216	BZ	0 548 596 A2	6/3/93	Europe					
1	CA	0 344 764	12/6/89	Europe					
	СВ	0 702 399	3/20/96	Europe					
	CC	GB 2 287 827	9/27/95	United Kingd	om				
	CD	JP52-12063		Japan					

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		OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)
748	CJ	Abstract of JP 3041729 published 2/22/91
	CK	Abstract of JP 1008630, published 1/12/89
	CL	Abstract of Japanese Appln. No. 63-16127 published July 31, 1989.
	СМ	Abstract of Japanese Appln. No. 52-100473 published March 14, 1979.
	CN	Abstract of Japanese Appln. No. 1-192712 published March 12, 1992.
17h8	СО	Translation/Abstract of Japanese Appln. No. 1984-125760 published January 10, 1986.

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LIST OF PATENTS AND OTHER ITEMS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT	APPLICANT: Eric J. Bergman	ARRY II
(Use several sheets if necessary)	FILING DATE: January 16, 2002	GROUP: 2002

		To a supply
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	101	Microttinography III. Technology for the Next Decade, Vol. 470, pp. 104-173 (1984)
	CZ	Baumgärtner, H., et al., "Ozone Cleaning of the SI-SIO <sub>2</sub> System," Appl. Phys. A, Vol. 43, pp. 223-226 (1987)
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HA	Dr	(HF/UVOC) Method (I) – Optimization of the HF Treatment-," <i>Japanese Journal of Applied Physics</i> , 28(12):2421-2424 (December 1989)
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## LIST OF PATENTS AND OTHER ITEMS FOR APPLOANT'S APPLOANT

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APPLICANT:

Eric J. Bergman FILING DATE:

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		I	W. W. W. C. I. C. COUNTY (PARENT)
$\mathcal{A}$	25	DI	Kern, Werner, "The Evolution of Silico Will Cleaning Technology," J. Electrochem. Soc., 197(6):1887-1892
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